

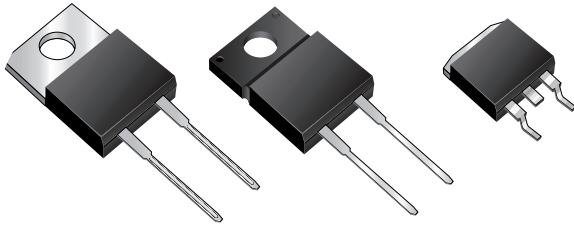


BYV29, BYV29F, BYV29B, UG8GT, UGF8GT, UGB8GT Series

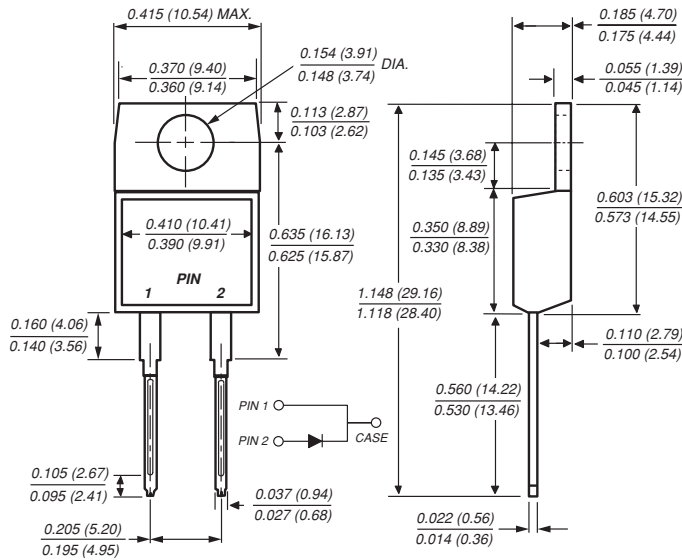
Vishay Semiconductors
formerly General Semiconductor

Ultrafast Rectifier

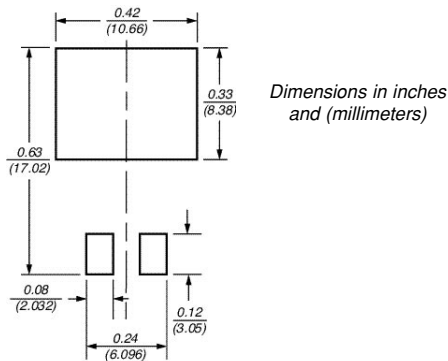
Reverse Voltage 300 to 400V
Forward Current 8.0A
Reverse Recovery Time 35ns



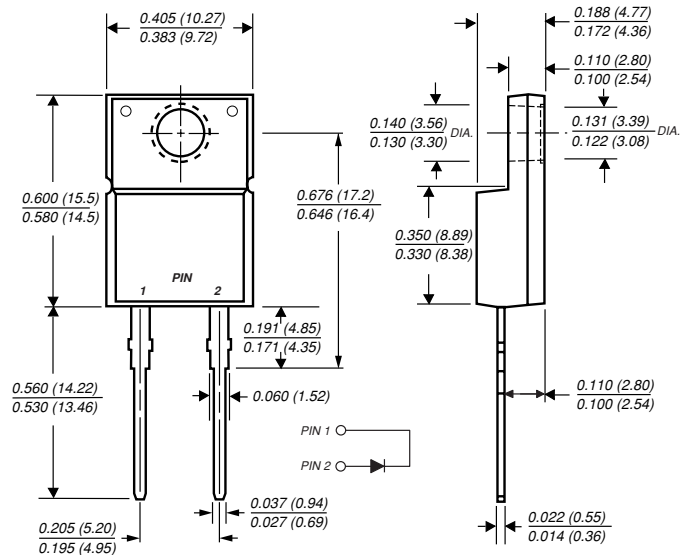
TO-220AC (BYV29, UG8 Series)



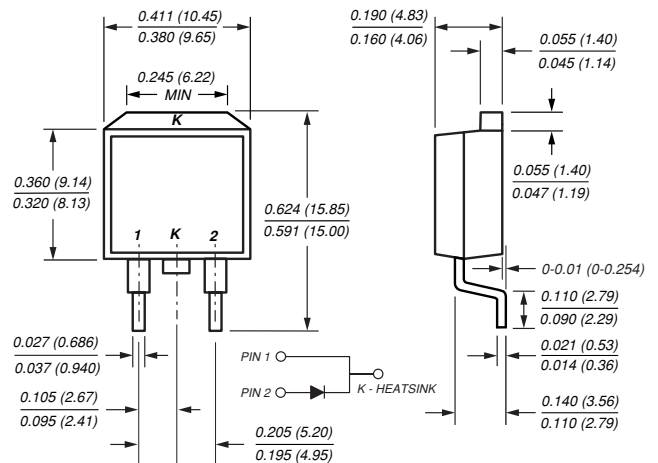
Mounting Pad Layout TO-263AB



ITO-220AC (BYV29F, UGF8 Series)



TO-263AB (BYV29B, UGB8 Series)



Features

- Plastic package has Underwriters Laboratories Flammability Classification 94V-0
- Ideally suited for freewheeling diode power factor correction applications
- Soft recovery characteristics
- Excellent high temperature switching
- Optimized to reduce switching losses
- High temperature soldering in accordance with CECC 802 / Reflow guaranteed
- Glass passivated chip junction

Mechanical Data

Case: JEDEC TO-220AC, ITO-220AC & TO-263AB molded plastic body

Terminals: Plated leads, solderable per MIL-STD-750, Method 2026

Polarity: As marked

Mounting Position: Any

Mounting Torque: 10 in-lbs maximum

Weight: 0.08 oz., 2.24 g

BYV29, BYV29F, BYV29B, UG8GT, UGF8GT, UGB8GT Series



Vishay Semiconductors
formerly General Semiconductor

Maximum Ratings (T_C = 25°C unless otherwise noted)

Parameter	Symbol	UG8FT	UG8GT	Unit
		BYV29-300	BYV29-400	
Maximum repetitive peak reverse voltage	V _{RRM}	300	400	V
Maximum working reverse voltage	V _{RWM}	300	400	V
Maximum RMS voltage	V _{RMS}	210	280	V
Maximum DC blocking voltage	V _{DC}	300	400	V
Maximum average forward rectified current at T _C = 100°C	I _{F(AV)}	8.0		A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method) at T _C = 100°C	I _{FSM}	110		A
Operating junction and storage temperature range	T _J , T _{STG}	-40 to +150		°C
RMS Isolation voltage (UGF & BYV29F types only) from terminals to heatsink with t = 1.0 second, RH ≤ 30%	V _{ISOL}	4500 ⁽¹⁾ 3500 ⁽²⁾ 1500 ⁽³⁾		V

Electrical Characteristics (T_C = 25°C unless otherwise noted)

Parameter	Symbol	UG8FT	UG8GT	Unit
		BYV29-300	BYV29-400	
Maximum instantaneous forward voltage ⁽⁴⁾ I _F = 8A, T _J = 25°C I _F = 8A, T _J = 150°C I _F = 20A, T _J = 25°C	V _F	1.25 1.03 1.40		V
Maximum DC reverse current at V _{RRM} T _C = 25°C T _C = 100°C	I _R	10 350		μA
Maximum reverse recovery time at I _F = 0.5A, I _R = 1.0A, I _{rr} = 0.25A	t _{rr}	35		ns
Maximum reverse recovery time at I _F = 1.0A, di/dt = 100A/μs, V _R = 30V, I _{rr} = 0.1 I _{RM}	t _{rr}	50		ns
Maximum reverse recovery current at I _F = 10A, di/dt = 50A/μs, V _R = 30V, T _C = 100°C	I _{RM}	5.5		A
Maximum recovered stored charged at I _F = 2A, di/dt = 20A/μs, V _R = 30V, I _{rr} = 0.1 I _{RM}	Q _{rr}	55		nC

Thermal Characteristics (T_C = 25°C unless otherwise noted)

Parameter	Symbol	UG8	UGF8	UGB8	Unit
		BYV29	BYV29F	BYV29B	
Typical thermal resistance from junction to case	R _{θJC}	2.5	5.5	2.5	°C/W

Notes:

- (1) Clip mounting (on case), where lead does not overlap heatsink with 0.110" offset
- (2) Clip mounting (on case), where leads do overlap heatsink
- (3) Screw mounting with 4-40 screw, where washer diameter is ≤ 4.9 mm (0.19")
- (4) Pulse test: 300μs pulse width, 1% duty cycle



Ratings and Characteristic Curves ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Fig. 1 – Maximum Forward Current Derating Curve

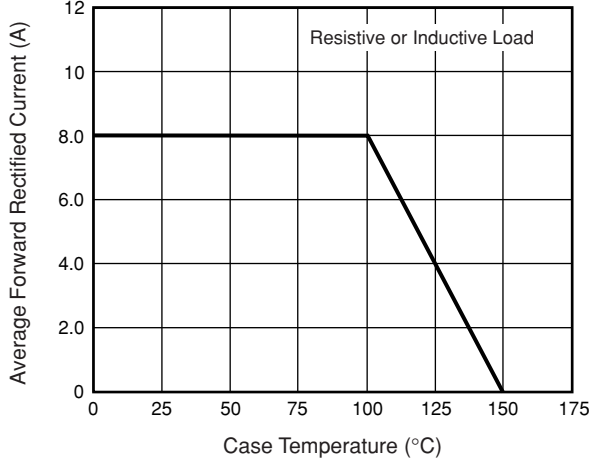


Fig. 2 – Maximum Non-Repetitive Peak Forward Surge Current

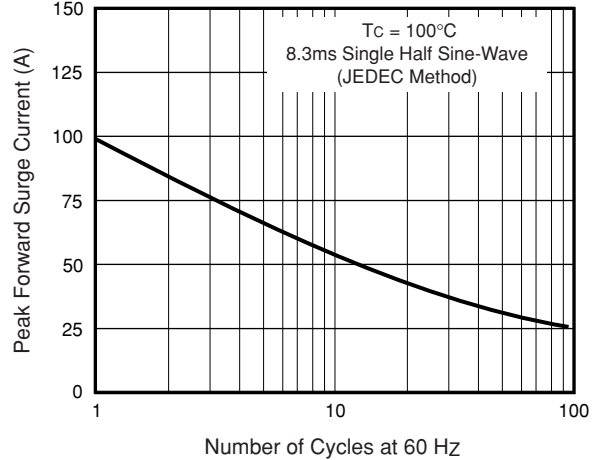


Fig. 3 – Typical Instantaneous Forward Characteristics

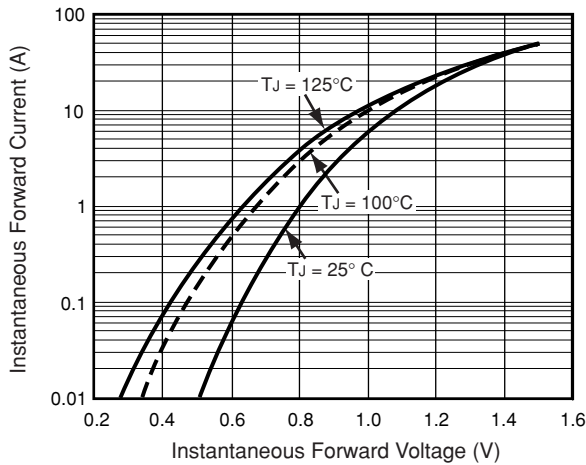


Fig. 4 – Typical Reverse Leakage Characteristics

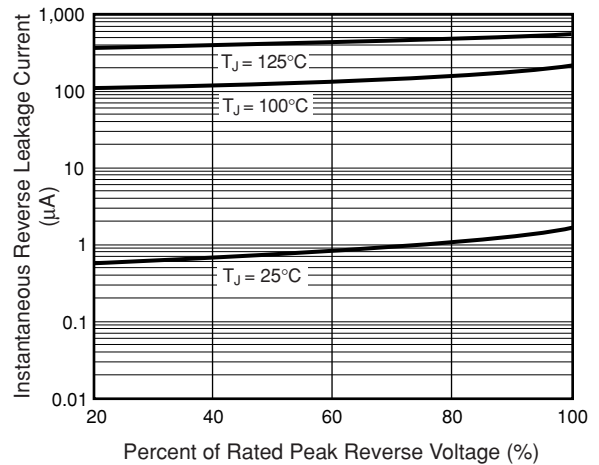


Fig 5 – Reverse Switching Characteristics Per Leg

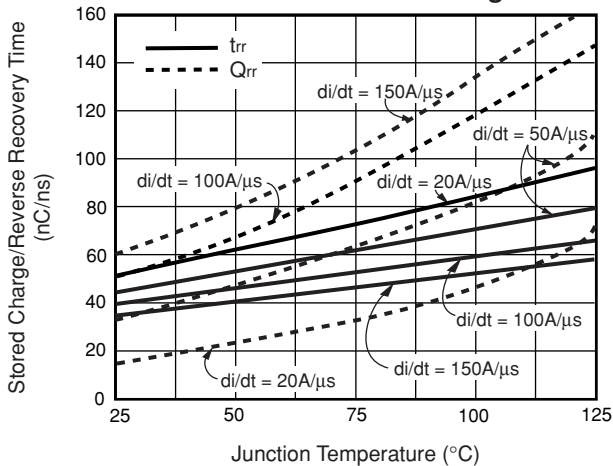
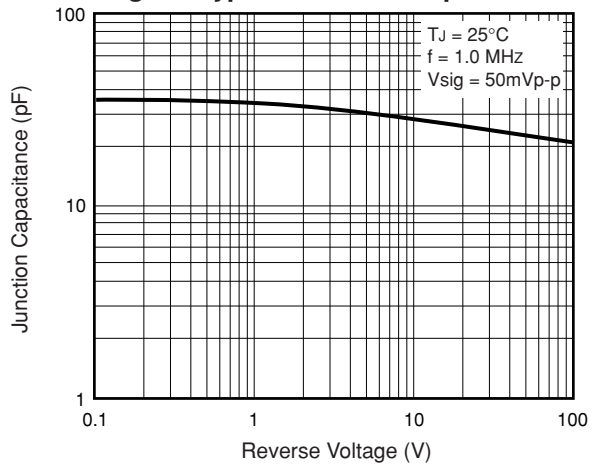


Fig. 6 – Typical Junction Capacitance





LittleDiode supplies new, hard to find or obsolete electronic components and semiconductors all over the world.

With over two million different components listed you are sure to find the part you need.

Feel free to visit us today at our online store:

LittleDiode.com

Looking forward to providing you with the best possible service.